

# MMBT3904LT1

Preferred Device

## General Purpose Transistor

### NPN Silicon

#### Features

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Base Voltage	$V_{CBO}$	60	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	$I_C$	200	mA dc

#### THERMAL CHARACTERISTICS

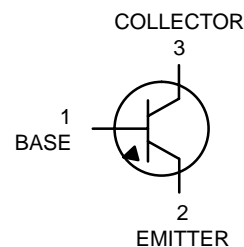
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

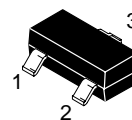


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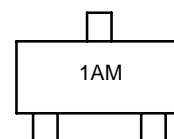
<http://onsemi.com>



#### MARKING DIAGRAM



SOT-23 (TO-236)  
CASE 318  
Style 6



CE = Specific Device Code

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT3904LT1	SOT-23	3000 / Tape & Reel
MMBT3904LT1G	SOT-23	3000 / Tape & Reel
MMBT3904LT3	SOT-23	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# MMBT3904LT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector – Emitter Breakdown Voltage (Note 4) ( $I_C = 1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	60	–	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ )	$I_{BL}$	–	50	nAdc
Collector Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ )	$I_{CEX}$	–	50	nAdc

## ON CHARACTERISTICS (Note 4)

DC Current Gain (Note 3) ( $I_C = 0.1\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 50\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 100\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ )	$H_{FE}$	40 70 100 60 30	– – 300 – –	–
Collector – Emitter Saturation Voltage (Note 4) ( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ ) ( $I_C = 50\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{CE(sat)}$	– –	0.2 0.3	Vdc
Base – Emitter Saturation Voltage (Note 4) ( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ ) ( $I_C = 50\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{BE(sat)}$	0.65 –	0.85 0.95	Vdc

## SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	300	–	MHz
Output Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	4.0	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	–	8.0	pF
Input Impedance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mA}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	1.0	10	k ohms
Voltage Feedback Ratio ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mA}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	0.5	8.0	$\times 10^{-4}$
Small – Signal Current Gain ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mA}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	100	400	–
Output Admittance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 1.0\text{ mA}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	1.0	40	$\mu\text{mhos}$
Noise Figure ( $V_{CE} = 5.0\text{ Vdc}$ , $I_C = 100\text{ }\mu\text{A}$ , $R_S = 1.0\text{ k ohms}$ , $f = 1.0\text{ kHz}$ )	NF	–	5.0	dB

## SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0\text{ Vdc}$ , $V_{BE} = -0.5\text{ Vdc}$ , $I_C = 10\text{ mA}$ , $I_{B1} = 1.0\text{ mA}$ )	$t_d$	–	35	ns
Rise Time		$t_r$	–	35	
Storage Time	$(V_{CC} = 3.0\text{ Vdc}$ , $I_C = 10\text{ mA}$ , $I_{B1} = I_{B2} = 1.0\text{ mA}$ )	$t_s$	–	200	ns
Fall Time		$t_f$	–	50	

3.  $FR-5 = 1.0 \times 0.75 \times 0.062\text{ in.}$

4. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

# MMBT3904LT1

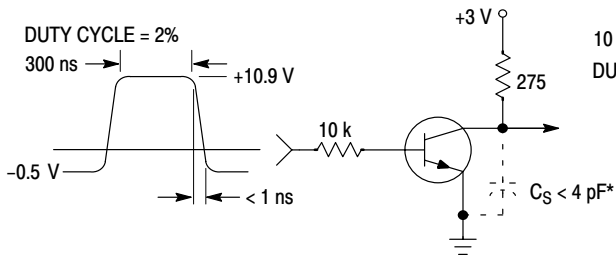


Figure 1. Delay and Rise Time Equivalent Test Circuit

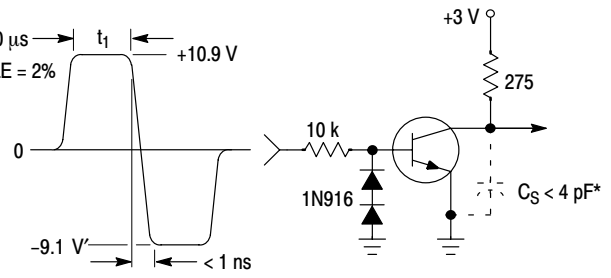


Figure 2. Storage and Fall Time Equivalent Test Circuit

\* Total shunt capacitance of test jig and connectors

## TYPICAL TRANSIENT CHARACTERISTICS

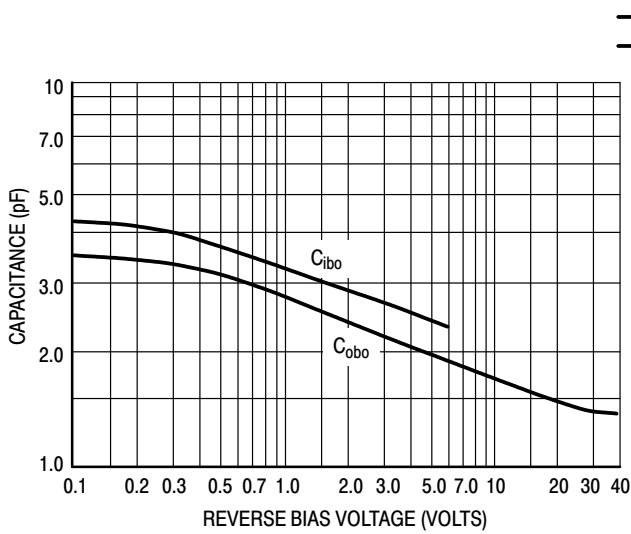


Figure 3. Capacitance

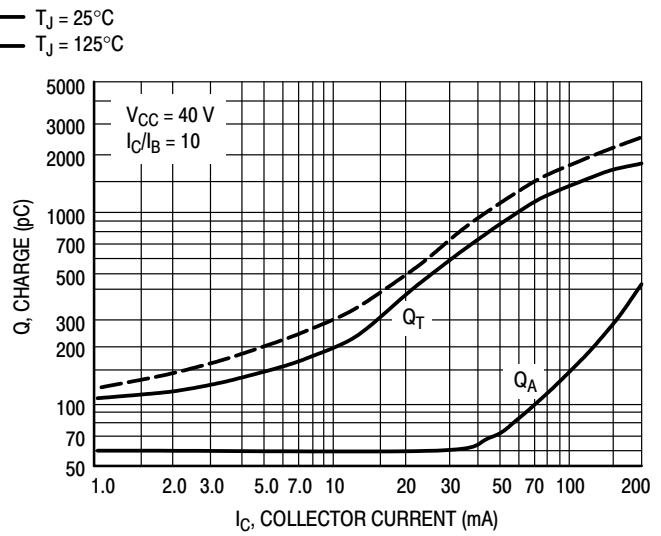


Figure 4. Charge Data

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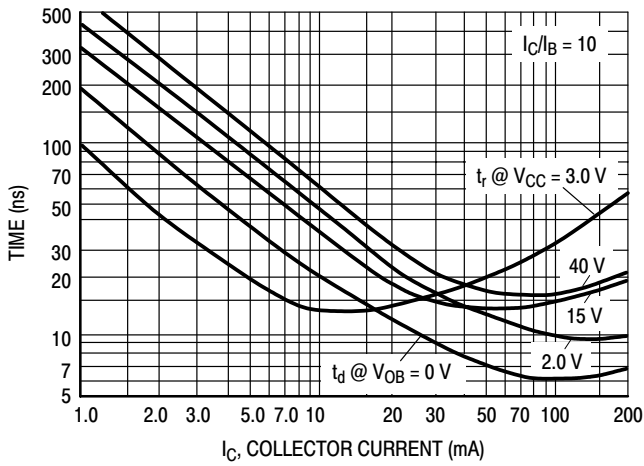


Figure 5. Turn-On Time

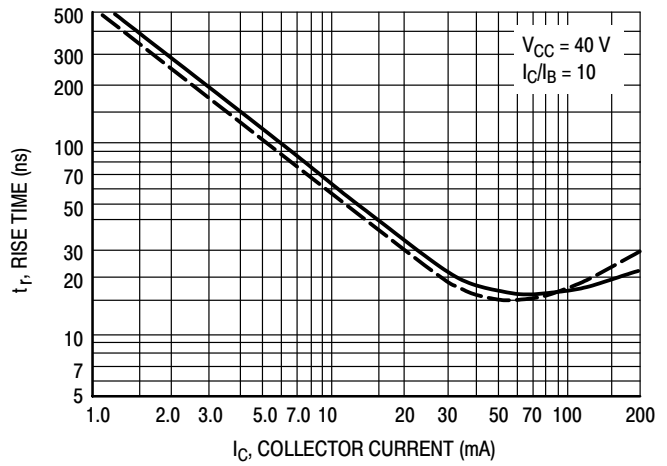


Figure 6. Rise Time

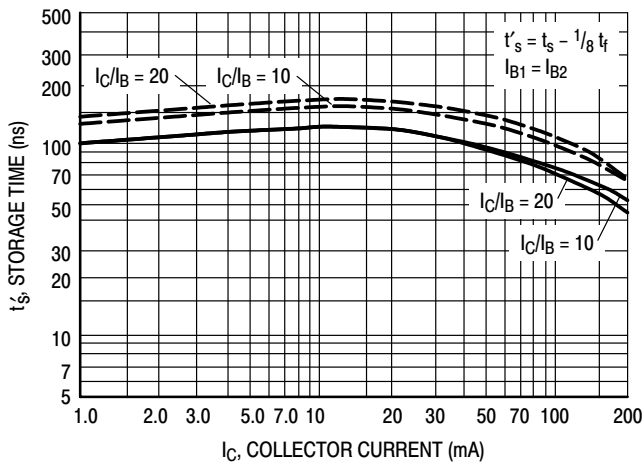


Figure 7. Storage Time

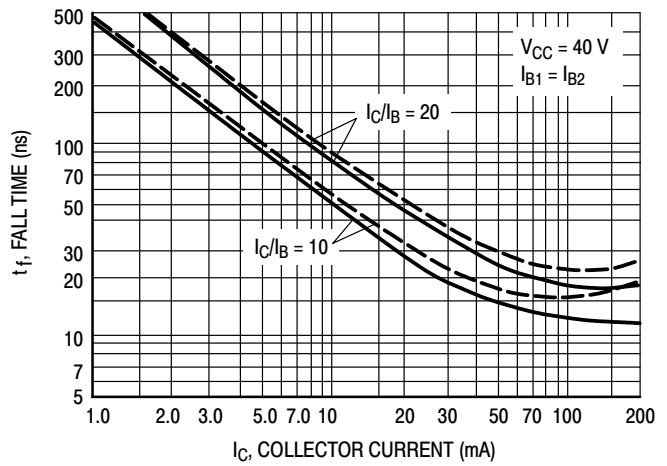


Figure 8. Fall Time

## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = 5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

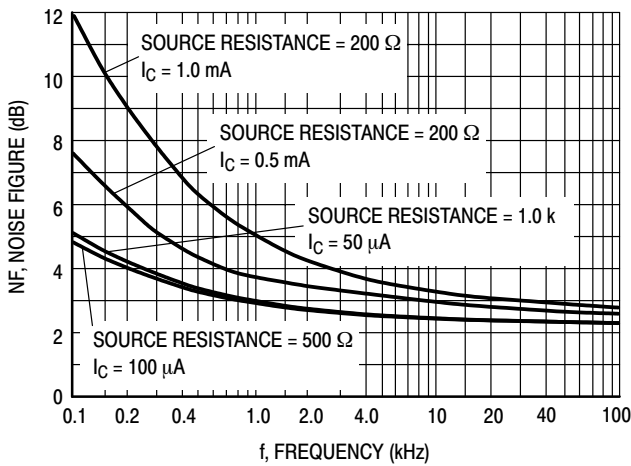


Figure 9.

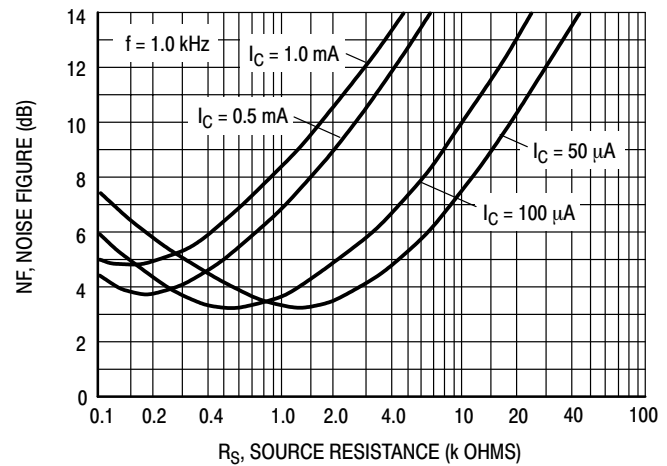


Figure 10.

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## h PARAMETERS

( $V_{CE} = 10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$ )

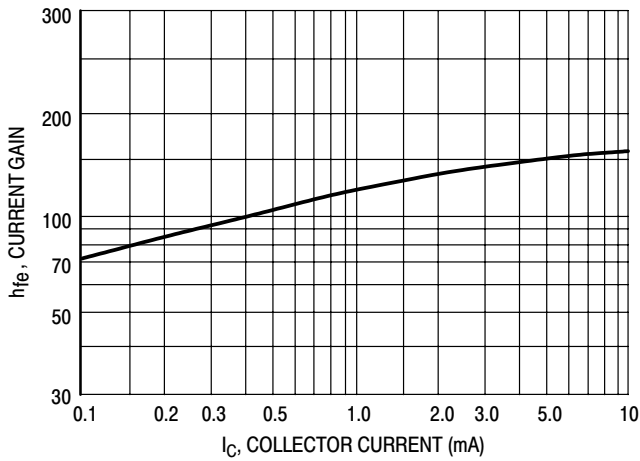


Figure 11. Current Gain

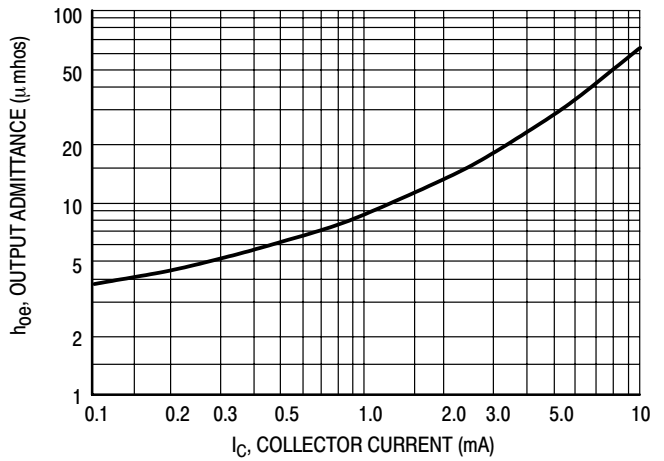


Figure 12. Output Admittance

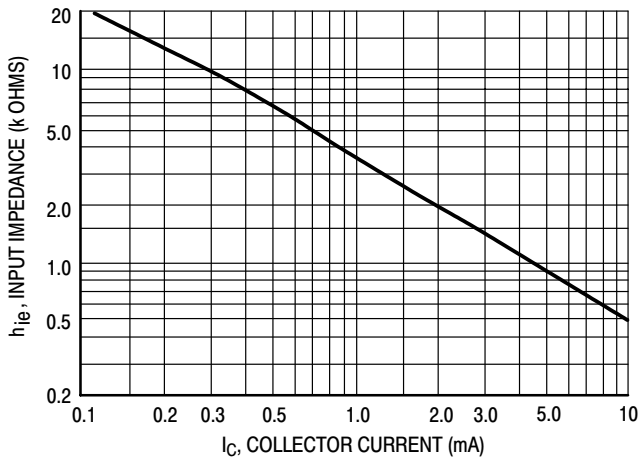


Figure 13. Input Impedance

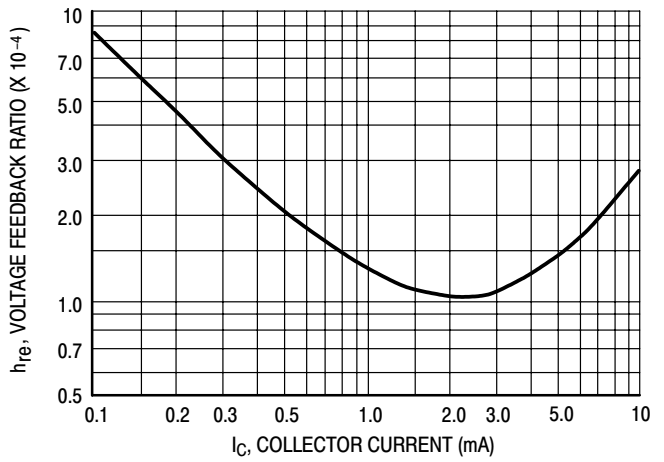


Figure 14. Voltage Feedback Ratio

## TYPICAL STATIC CHARACTERISTICS

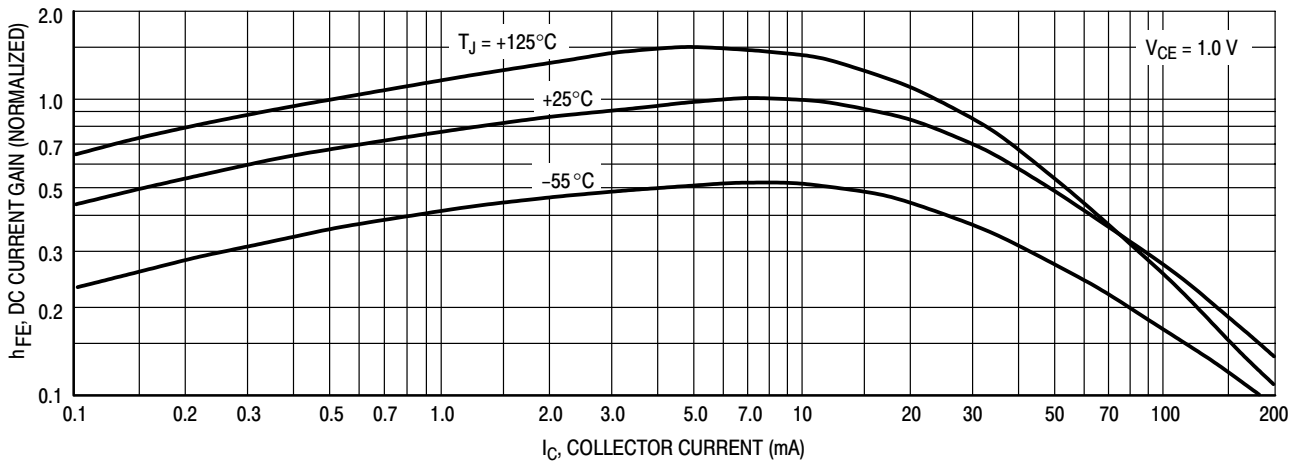


Figure 15. DC Current Gain

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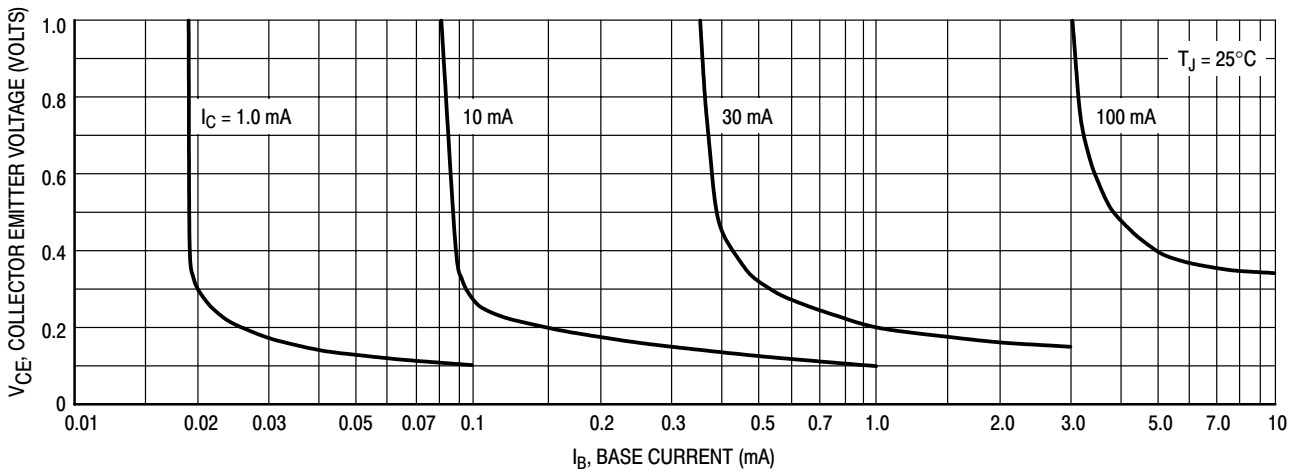


Figure 16. Collector Saturation Region

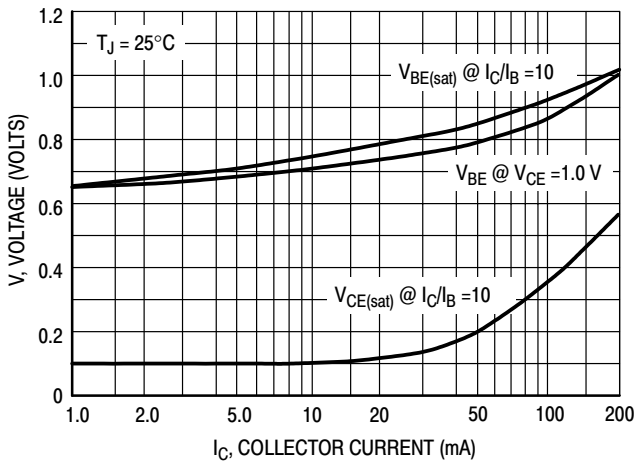


Figure 17. "ON" Voltages

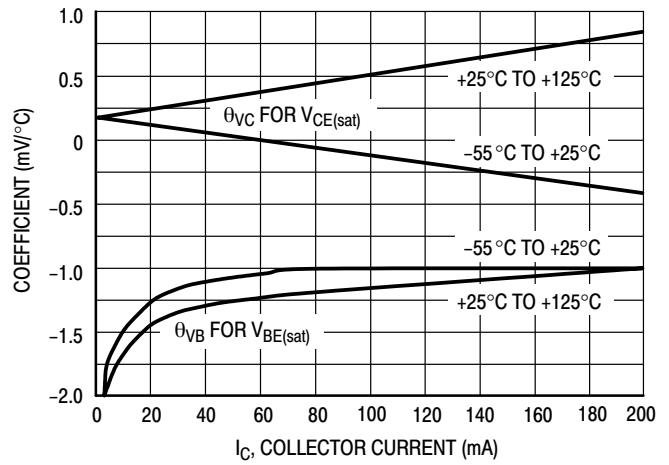


Figure 18. Temperature Coefficients

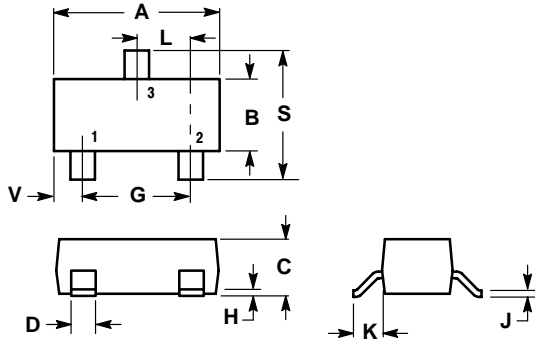
# MMBT3904LT1

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AH

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

### SOLDERING FOOTPRINT\*

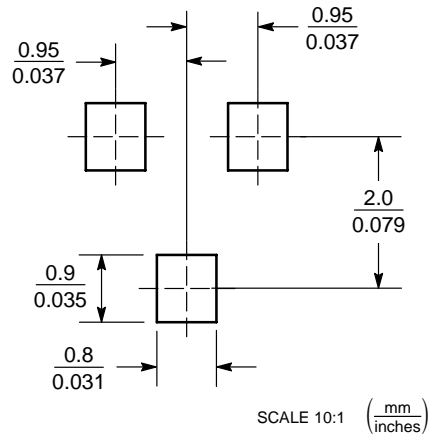


Figure 19. SOT-23

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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